imall

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



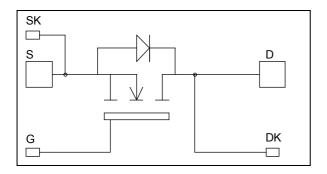
Contact us

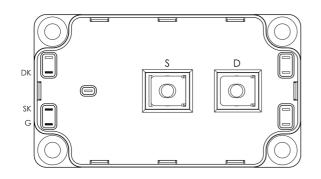
Tel: +86-755-8981 8866 Fax: +86-755-8427 6832 Email & Skype: info@chipsmall.com Web: www.chipsmall.com Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China





Single Switch MOSFET Power Module





$V_{DSS} = 500V$ $R_{DSon} = 9 \text{ m}\Omega \text{ typ} @ \text{Tj} = 25^{\circ}\text{C}$ $I_D = 497\text{A} @ \text{Tc} = 25^{\circ}\text{C}$

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Power MOS 7[®] FREDFETs
 - Low R_{DSon}
 - Low input and Miller capacitance
 - Low gate charge
 - Fast intrinsic reverse diode
 - Avalanche energy rated
 - Very rugged
 - Kelvin source for easy drive
 - Very low stray inductance
 - Symmetrical design
 - M5 power connectors
 - High level of integration
 - AlN substrate for improved thermal performance

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Low profile
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V _{DSS}	Drain - Source Breakdown Voltage		500	V
I _D	Continuous Drain Current	$T_c = 25^{\circ}C$	497	
ID	Continuous Drain Current	$T_c = 80^{\circ}C$	371	А
I _{DM}	Pulsed Drain current		1988	
V _{GS}	Gate - Source Voltage		±30	V
R _{DSon}	Drain - Source ON Resistance		10	mΩ
PD	Maximum Power Dissipation $T_c = 25^{\circ}C$		5000	W
I _{AR}	Avalanche current (repetitive and non repetitive)		71	А
E _{AR}	Repetitive Avalanche Energy		50	mJ
E _{AS}	Single Pulse Avalanche Energy		3000	IIIJ

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I _{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 500V$	$T_j = 25^{\circ}C$			600	μA
		$V_{GS} = 0V, V_{DS} = 400V$	$T_j = 125^{\circ}C$			3000	
R _{DS(on)}	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 248.5A$			9	10	mΩ
V _{GS(th)}	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 30 \text{mA}$		3		5	V
I _{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 30 V, V_{DS} = 0V$				±450	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit	
C _{iss}	Input Capacitance	$V_{GS} = 0V$		63.3			
C _{oss}	Output Capacitance	$V_{\rm DS} = 25V$		12.4		nF	
C _{rss}	Reverse Transfer Capacitance	f = 1 MHz		0.63			
Qg	Total gate Charge	$V_{GS} = 10V$		1200		nC	
Q _{gs}	Gate – Source Charge	$V_{Bus} = 250V$		300			
Q_{gd}	Gate – Drain Charge	I _D =497A		630			
T _{d(on)}	Turn-on Delay Time	Inductive switching @ 125°C		21			
T _r	Rise Time	$\begin{split} V_{GS} &= 15V \\ V_{Bus} &= 333V \\ I_D &= 497A \\ R_G &= 0.5\Omega \end{split}$		42		ns	
T _{d(off)}	Turn-off Delay Time			96			
T_{f}	Fall Time			100			
Eon	Turn-on Switching Energy	Inductive switching (a) $25^{\circ}C$		6			
$\mathrm{E}_{\mathrm{off}}$	Turn-off Switching Energy	$V_{GS} = 15V, V_{Bus} = 333V$ $I_D = 497A, R_G = 0.5\Omega$		6.2		mJ	
Eon	Turn-on Switching Energy	Inductive switching @ 125°C $V_{GS} = 15V$, $V_{Bus} = 333V$ $I_D = 497A$, $R_G = 0.5\Omega$		9.48		mI	
$\mathrm{E}_{\mathrm{off}}$	Turn-off Switching Energy			6.96		mJ	

Source - Drain diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
Is	Continuous Source current		$Tc = 25^{\circ}C$			497	А
	(Body diode)		$Tc = 80^{\circ}C$			371	A
V _{SD}	Diode Forward Voltage	$V_{GS} = 0V, I_S = -497A$				1.3	V
dv/dt	Peak Diode Recovery 1					18	V/ns
t _{rr}	Reverse Recovery Time		$T_j = 25^{\circ}C$			300	na
	Reverse Recovery Time	$I_{\rm S} = -497 {\rm A}$ $V_{\rm R} = 333 {\rm V}$	$T_j = 125^{\circ}C$			600	ns
Q _{rr}	Devenue Deservent Change	$di_{s}/dt = 600A/\mu s$	$T_j = 25^{\circ}C$		15.6		uС
	Reverse Recovery Charge	5	$T_{i} = 125^{\circ}C$		60		μC

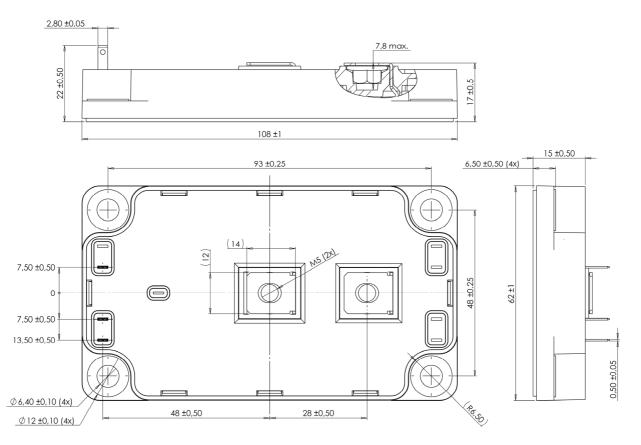
• dv/dt numbers reflect the limitations of the circuit rather than the device itself. $I_S \leq -497A$ di/dt $\leq 700A/\mu s$ $V_R \leq V_{DSS}$ $T_j \leq 150^{\circ}C$



Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
R _{thJC}	Junction to Case Thermal Resistance					0.025	°C/W
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
TJ	Operating junction temperature range			-40		150	
T _{STG}	Storage Temperature Range					125	°C
T _C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To Heatsink	M6	3		5	N.m
		For teminals	M5	2		3.5	19.111
Wt	Package Weight					300	g

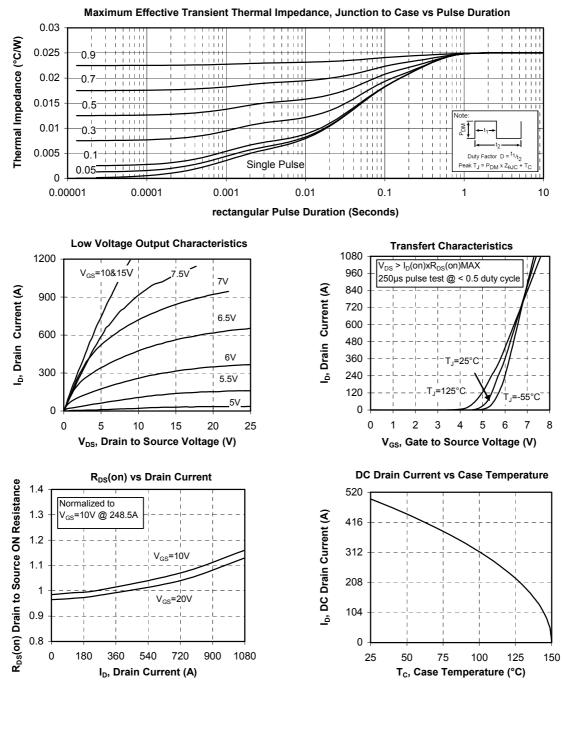
SP6 Package outline (dimensions in mm)



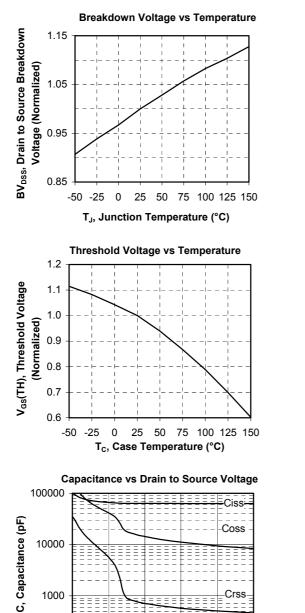
See application note APT0601 - Mounting Instructions for SP6 Power Modules on www.microsemi.com



Typical Performance Curve







100

0

10

20

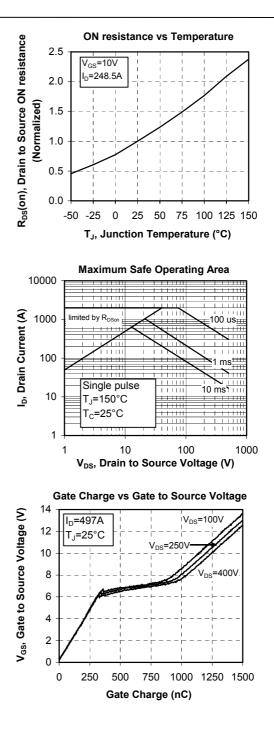
V_{DS}, Drain to Source Voltage (V)

30

40

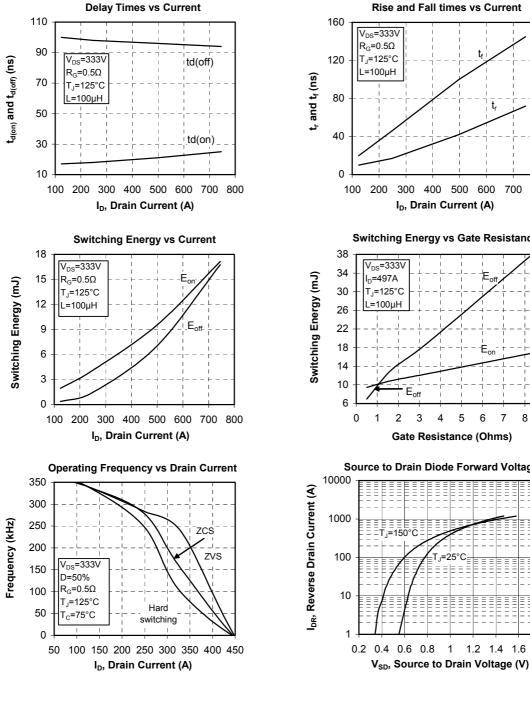
50

APTM50UM09FAG





t



300 400 500 600 700 800 I_D, Drain Current (A) Switching Energy vs Gate Resistance 8 9 4 5 6 7 Gate Resistance (Ohms) Source to Drain Diode Forward Voltage

www.microsemi.com

1.2 1.4 1.6 1.8

1



DISCLAIMER

The information contained in the document (unless it is publicly available on the Web without access restrictions) is PROPRIETARY AND CONFIDENTIAL information of Microsemi and cannot be copied, published, uploaded, posted, transmitted, distributed or disclosed or used without the express duly signed written consent of Microsemi. If the recipient of this document has entered into a disclosure agreement with Microsemi, then the terms of such Agreement will also apply. This document and the information contained herein may not be modified, by any person other than authorized personnel of Microsemi. No license under any patent, copyright, trade secret or other intellectual property right is granted to or conferred upon you by disclosure or delivery of the information, either expressly, by implication, inducement, estoppels or otherwise. Any license under such intellectual property rights must be approved by Microsemi in writing signed by an officer of Microsemi.

Microsemi reserves the right to change the configuration, functionality and performance of its products at anytime without any notice. This product has been subject to limited testing and should not be used in conjunction with lifesupport or other mission-critical equipment or applications. Microsemi assumes no liability whatsoever, and Microsemi disclaims any express or implied warranty, relating to sale and/or use of Microsemi products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright or other intellectual property right. Any performance specifications believed to be reliable but are not verified and customer or user must conduct and complete all performance and other testing of this product as well as any user or customers final application. User or customer shall not rely on any data and performance specifications or parameters provided by Microsemi. It is the customer's and user's responsibility to independently determine suitability of any Microsemi product and to test and verify the same. The information contained herein is provided "AS IS, WHERE IS" and with all faults, and the entire risk associated with such information is entirely with the User. Microsemi specifically disclaims any liability of any kind including for consequential, incidental and punitive damages as well as lost profit. The product is subject to other terms and conditions which can be located on the web at http://www.microsemi.com/legal/tnc.asp

Life Support Application

Seller's Products are not designed, intended, or authorized for use as components in systems intended for space, aviation, surgical implant into the body, in other applications intended to support or sustain life, or for any other application in which the failure of the Seller's Product could create a situation where personal injury, death or property damage or loss may occur (collectively "Life Support Applications").

Buyer agrees not to use Products in any Life Support Applications and to the extent it does it shall conduct extensive testing of the Product in such applications and further agrees to indemnify and hold Seller, and its officers, employees, subsidiaries, affiliates, agents, sales representatives and distributors harmless against all claims, costs, damages and expenses, and attorneys' fees and costs arising, directly or directly, out of any claims of personal injury, death, damage or otherwise associated with the use of the goods in Life Support Applications, even if such claim includes allegations that Seller was negligent regarding the design or manufacture of the goods.

Buyer must notify Seller in writing before using Seller's Products in Life Support Applications. Seller will study with Buyer alternative solutions to meet Buyer application specification based on Sellers sales conditions applicable for the new proposed specific part.